Electronic Transport using first-principles method in Carbon Nanotube [5,5] coupled boron and nitrogen nanowire

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ABSTRACT

In the creation of a molecular rectification diode by Aviram and Ratner in 1974, the miniaturization of circuits components as concerns of electronic transport of molecular junctions opened many new possibilities for the study of quantum interference phenomena and electronic behavior in atomic scale from the novel nanodevices development for application industrial [1]. In this work, it was realized a theoretical study about the electronics proprieties of wires junctions composed by atoms of boron and nitrogen with electrodes of a metallic carbon nanotube. However though, through of analyses of current-voltage, differential conductance, transmittance and the frontier molecular orbital, obtained through non-equilibrium green function with combined density functional method (NEGF-DFT) with formalism pertaining to Landauer-Buttiker [2,3] in the implementation of the SIESTA/TRANSIESTA package [4], it was observed negative differential resistance (NDR)[5], with an initial peak in values followed by a deterioration around 0.08V compared to the development of other studies [6,7]. This property occurs by aligning the system's Fermi level with the Frontier molecular orbital (FMO) [8]. This effect suggests applications in nano circuit compounds, as well as promising applications in photocatalysis, due to their resistance to chemical and physical modifications in the environment [9]. Therefore, this shows us good results for use in molecule engineering and plate component manufacturing.

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